

	Hits	Search Text	DBs
2	861	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4) same (substrate or wafer or underlayer or workpiece or support) same first same (second or overcoat\$2 or topcoat\$4) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4)	US-PGPUB; USPAT
3	3	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4) same (substrate or wafer or underlayer or workpiece or support) same first same (second or overcoat\$2 or topcoat\$4) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and methylacrylamide	US-PGPUB; USPAT
4	8	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4) same (substrate or wafer or underlayer or workpiece or support) same first same (second or overcoat\$2 or topcoat\$4) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and methylacrylamide	US-PGPUB; USPAT

	Hits	Search Text	DBs
5	61	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4) same (substrate or wafer or underlayer or workpiece or support) same (second or overcoat\$2 or topcoat\$4) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and methylacrylamide	US-PGPUB; USPAT
6	8	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4) same (substrate or wafer or underlayer or workpiece or support) same first same (second or overcoat\$2 or topcoat\$4) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and methylacrylamide	US-PGPUB; USPAT
7	34	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4 or CAR) same (substrate or wafer or underlayer or workpiece or support) same first) and ((second or overcoat\$2 or topcoat\$4) same (resist or photoresist) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and \$7methylacrylamide	US-PGPUB; USPAT

	Hits	Search Text	DBs
8	88	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4 or CAR) same (substrate or wafer or underlayer or workpiece or support or bottom or first)) and (((second or overcoat\$2 or topcoat\$4) with (resist or photoresist)) or (top near3resist) or (bi\$1layer near3 \$4resist)) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and \$7methyacrylamide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
9	28	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4 or CAR) same (substrate or wafer or underlayer or workpiece or support) same (bottom or first)) and (((second or overcoat\$2 or topcoat\$4) with (resist or photoresist)) or (top near3 resist) or (bi\$1layer near3 \$4resist)) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and \$7methyacrylamide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
10	82	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4 or CAR) same (substrate or wafer or underlayer or workpiece or support or bottom or first)) and (((second or overcoat\$2 or topcoat\$4) with (resist or photoresist)) or (top near3 resist) or (bi\$1layer near3 \$4resist)) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and \$7methylacrylamide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
11	11	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4 or CAR) same (substrate or wafer or underlayer or workpiece or support or bottom or first)) and (((second or overcoat\$2 or topcoat\$4) with (resist or photoresist)) or (top near3 resist) or (bi\$1layer near3 \$4resist)) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and \$7dimethylacrylamide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
12	17	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4 or CAR) same (substrate or wafer or underlayer or workpiece or support or bottom or first)) and (((second or overcoat\$2 or topcoat\$4 or upper) with (resist or photoresist)) or (top near3 resist) or (bi\$1layer near3 \$4resist)) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and \$7dimethylacrylamide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
13	17	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4 or CAR) same (substrate or wafer or underlayer or workpiece or support or bottom or first)) and (((second or overcoat\$2 or topcoat\$4 or upper) with (resist or photoresist)) or (top near3 resist) or (bi\$1layer near3 \$4resist)) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and \$7dimethylacrylamide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
14	17	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4 or CAR) same (substrate or wafer or underlayer or workpiece or support or bottom or first)) and (((second or overcoat\$2 or topcoat\$4 or upper) with (resist or photoresist)) or (top near3 resist) or (bi\$1layer near3 \$4resist)) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and \$7dimethylacrylamide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB
15	0	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4 or CAR) same (substrate or wafer or underlayer or workpiece or support or bottom or first)) and (((second or overcoat\$2 or topcoat\$4 or overly\$3) with (resist or photoresist)) or (top near3 resist) or (bi\$1layer near3 \$4resist)) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and (\$7dimethylacrylamide same solvent same water)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB

	Hits	Search Text	DBs
16	5	((photoresist or resist or (chemical\$3 near4 amplif\$6 near3 \$4resist) or PAG or acid\$3generat\$4 or CAR) same (substrate or wafer or underlayer or workpiece or support or bottom or first)) and (((second or overcoat\$2 or topcoat\$4 or overly\$3) with (resist or photoresist)) or (top near3 resist) or (bi\$1layer near3 \$4resist)) same (solvent or water) same expos\$4 same (post\$2expos\$4bak\$4 or PEB or bak\$4 or heat\$4 or thermal\$6 or anneal\$4) same develop\$4) and \$7dimethylacrylamide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB